Silicon tracker development from ALICE towards FCC-ee



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Outline



- ALICE Upgrades and FCC-ee common challenges
- ITS3: ALICE vertex detector upgrade for LHC Run 4
 - Ultra-thin, truly cylindrical, wafer-scale MAPS
- ALICE 3: future heavy-ion experiment for LHC Run 5 and beyond
 - Compact all-silicon MAPS tracker
- Conclusions and outlook



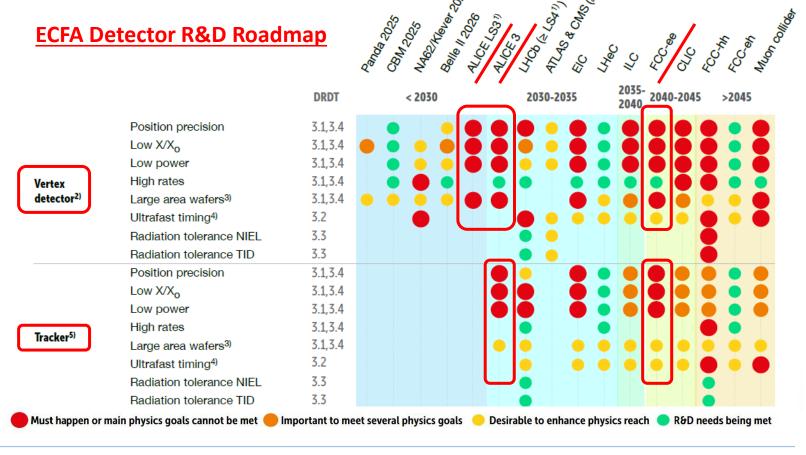


ALICE Upgrades and FCC-ee common challenges



 The ALICE silicon upgrades planned for LHC LS3 and LS4 and the FCC-ee vertex and tracker detectors are targeting similar performance

Can the R&D for ITS3 and ALICE 3 serve as a stepping stone for FCC-ee vertex and tracker detectors?











 The ALICE silicon upgrades planned for LHC LS3 and LS4 and the FCC-ee vertex and tracker detectors are targeting similar performance

Target performance	ITS3	ALICE 3	FCC-ee
Position precision	5 μm	2.5 μm	3 μm
X/X ₀ per layer	0.09% (average) 0.07% (most of active region)	0.1 %	0.15 - 0.3 %
Power consumption	40 mW/cm ² (active region)	20 mW/cm ²	50 mW/cm ²
NIEL	$10^{13}1\text{MeV}n_{\text{eq}}/\text{cm}^2$	10 ¹⁶ 1MeV n _{eq} /cm ² (<i>LOI</i> , *)	$\sim 6 \times 10^{12} 1$ MeV neq /cm ² /year
TID	1 Mrad	300 Mrad <i>(LOI, *)</i>	~3.4 Mrad/year
Maximum hit rate	< 10 MHz/cm ²	94 MHz/cm ²	400 MHz/cm ² (*)
Time resolution	<i>O</i> (1000 ns RMS)	<i>O</i> (100 ns RMS)	~20 ns RMS

* being revised





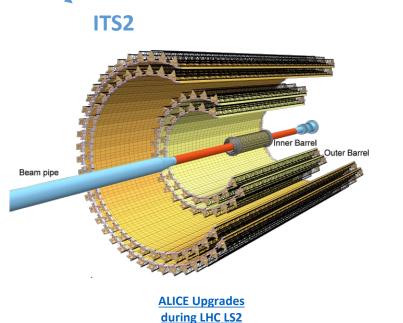
ALICE silicon tracker development path

ITS3

Cylindrical





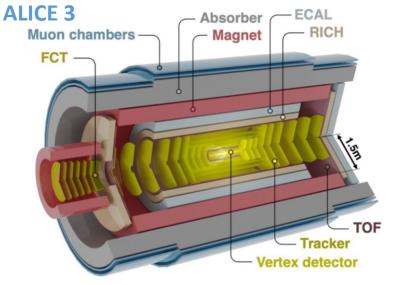


Half Barrels

BEAMPRE

Wastradel

LOI: <u>CERN-LHCC-2019-018</u> TDR: CERN-LHCC-2024-003



LOI: CERN-LHCC-2022-009
Scoping Document submitted to LHCC



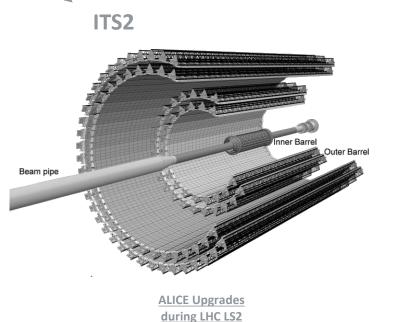
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ITS3

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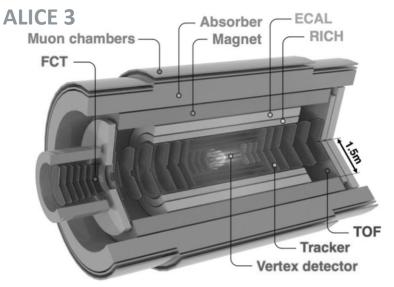
Half Barrels

REAMPIPE

Half Layer

Half Layer

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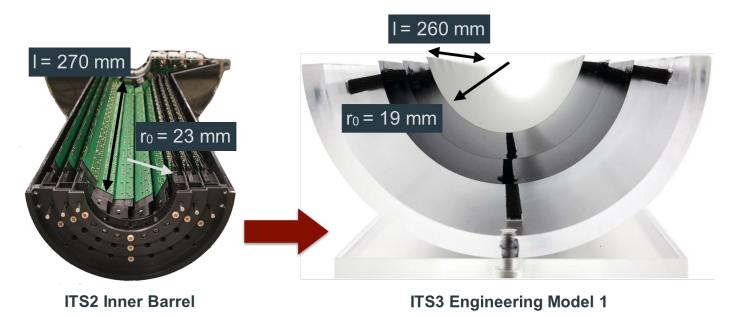


ITS3 layout and material budget



3 layers of curved wafer-scale MAPS in TPSCo 65 nm CMOS process

- Replacing ITS2 Inner Barrel (innermost radius reduced from 24 mm to 19 mm)
- Each half-layer made of one wafer-size flexible sensor
- In-silicon data transmission and power distribution
- Minimal carbon foam support structures
- Air cooling





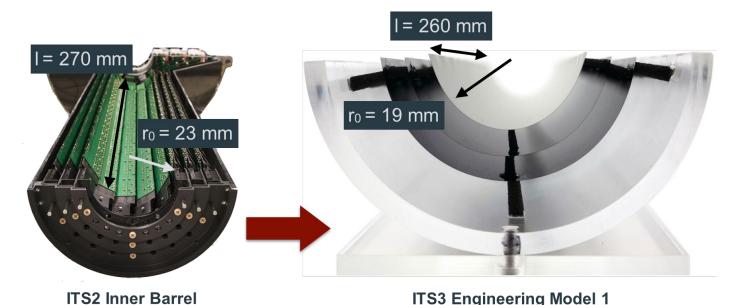


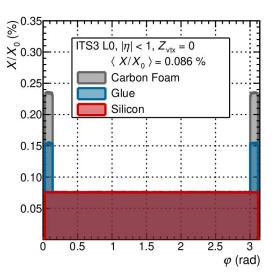
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Minimal material budget: ~0.09% X₀ on average

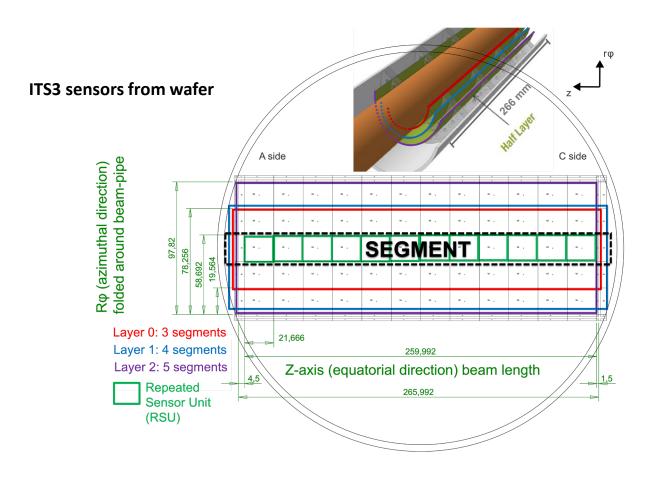




ITS3 layout and material budget



• 3 layers of curved wafer-scale MAPS in TPSCo 65 nm CMOS process





ITS3 Engineering Model 2

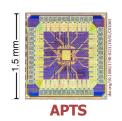




ITS3 chip development plan



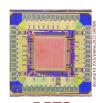
- Multi-Layer Run 1 (MLR1): first MAPS in TPSCo 65 nm CMOS
 - Transistor test structures
 - Analog and digital test structures
 - Achieved goal: full process qualification





we are

here!

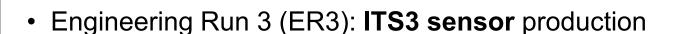


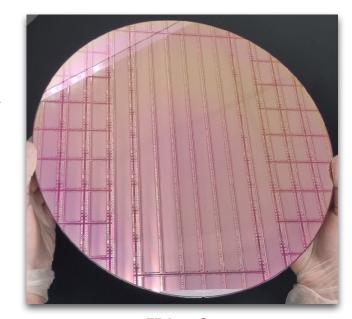
DPT

- Engineering Run 1 (ER1): first large area sensors
 - Main goals: excercize and validate stitching
 - Chips work, main yield issue understood
 - Full characterization currently ongoing



- Now: **specifications frozen**, design being finalized
- Submission to foundry planned for early 2025





ER1 wafer





65 nm CMOS process validation and radiation hardness



TPSCo 65 nm CMOS process validated on MLR1 test structures:

FCC-ee

 $\sim 6 \times 10^{12}$ 1 MeV neq /cm²/year



• Efficiency > 99%

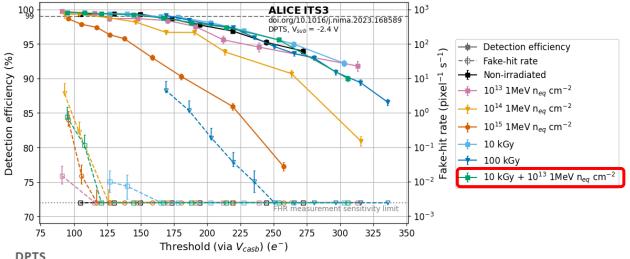
• Fake-hit rate < 2.10⁻³ pix⁻¹ s⁻¹

over a wide operating range

Radiation hardness demonstrated beyond 10 kGy + 10¹³ 1MeV n_{eq} cm⁻²

ITS3 requirement

• Still efficient with 10¹⁵ 1MeV n_{eq} cm⁻² at room temperature





Detection efficiency and fake-hit rate Vs threshold and irradiation levels, as measured on 15 μm pitch **Digital Pixel Test Structures (DPTS)**





ITS3 sensor performance: spatial resolution

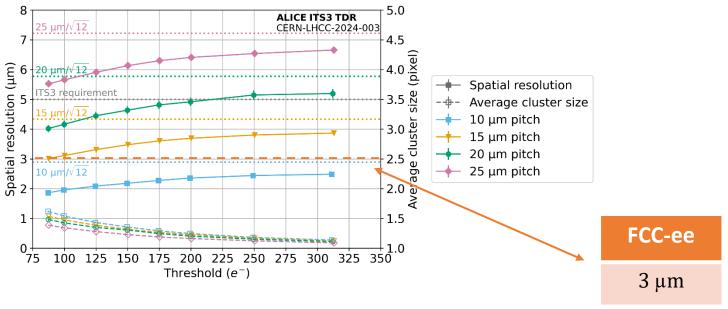


- ITS3 spatial resolution requirement: 5 μm
 - Test beam measurements on APTS with different pixel pitches
 - Requirement met for pitch ≤ 20 µm at standard operating settings
 - Projected resolution with (20.8 μm x 22.8 μm) ITS3 target pixel pitch meets the requirement





Spatial resolution Vs threshold and pixel pitch, as measured in testbeams on **APTS**



Sensor position stability required to be within 2 μm



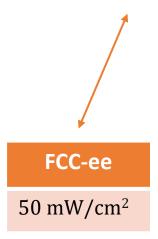


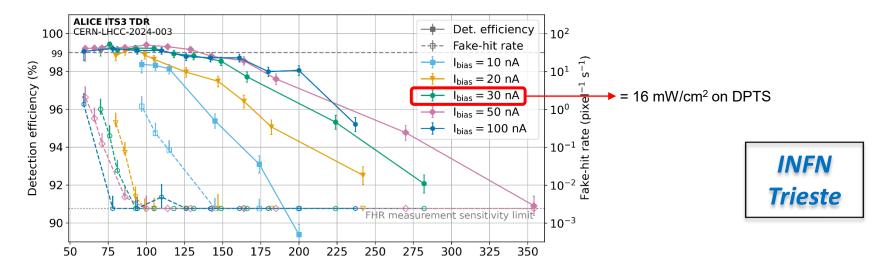
ITS3 sensor performance: power consumption



- ITS3 maximum **power density: 40 mW/cm²** in the pixel matrix
- In-pixel power consumption minimization studied on DPTS by optimizing front-end settings
 - 16 mW/cm² as measured on 15 μm pixel
 - 7.6 mW/cm² if projected to the final ITS3 sensor pixel pitch

to be measured on stitched sensor matrix







Detection efficiency and fake-hit rate Vs threshold and amplifier biasing current as measured on 15 μ m pitch **DPTS**



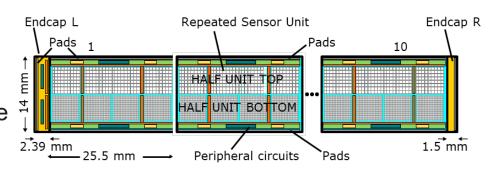


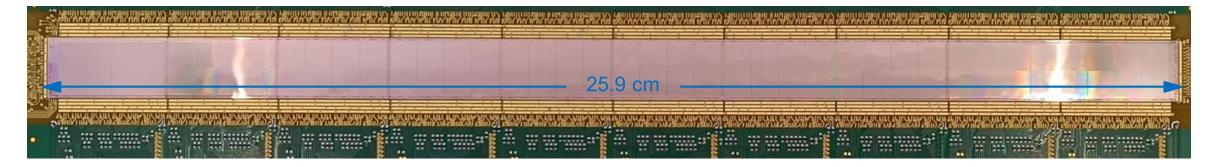
Threshold (e-)

ITS3 sensor performance: stitching



- MOnolithic Stitched Sensor (MOSS):
 - 10 Repeated Sensor Units (RSU) stitched together
 - **25.9 cm x 1.5 cm** 18 μm and 22.5 μm pitch 5 FE variants
 - Stitched backbone allows to control and read out from left edge
 - Each unit can be powered and tested separately
 - Main yield issue understood







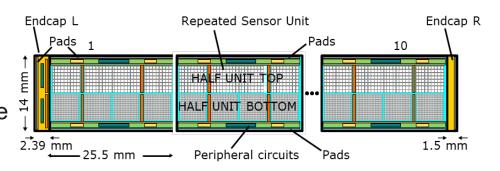


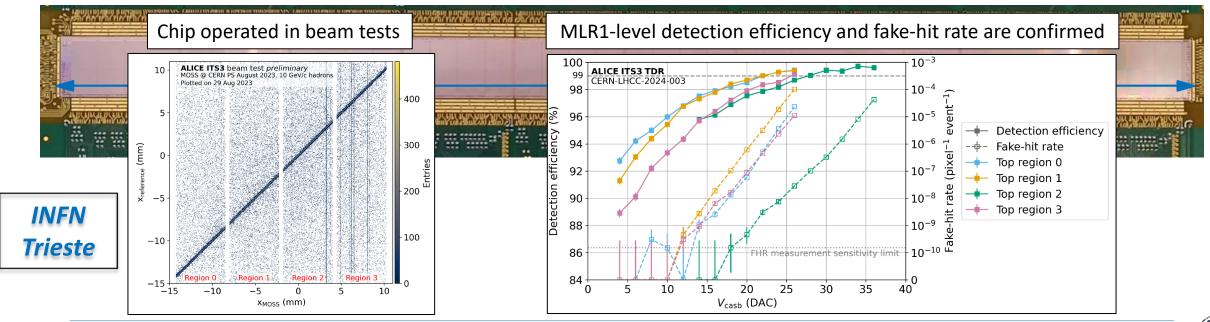
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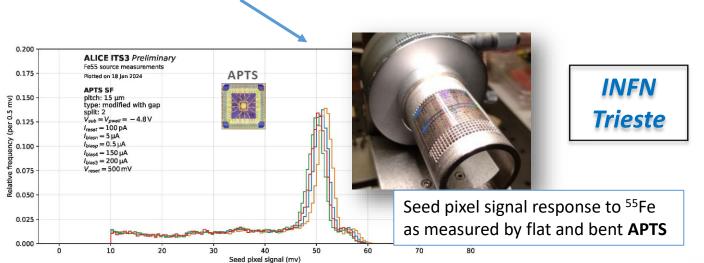


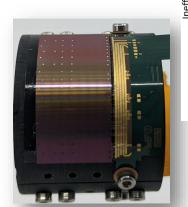


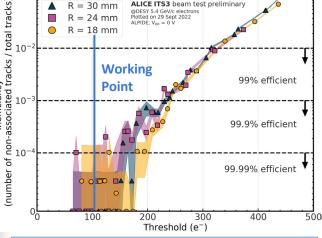
Bent MAPS: performance validation



- MAPS performance in curved geometry has been validated
 - Efficiency preserved on bent ALPIDE (180 nm CMOS sensors)
 - Charge collection properties preserved on bent APTS (65 nm CMOS)

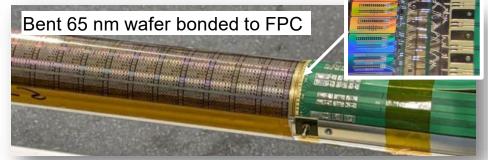






Detection inefficiency Vs threshold for curved 180 nm CMOS sensors (ALPIDE), bent beyond the ITS3 radii

- Large-area sensor bending
 - Technique and procedure have been mastered
 - Tests on functional bent stitched sensors in preparation

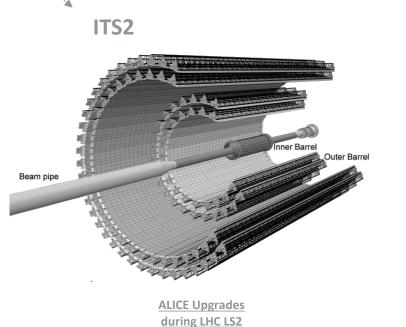


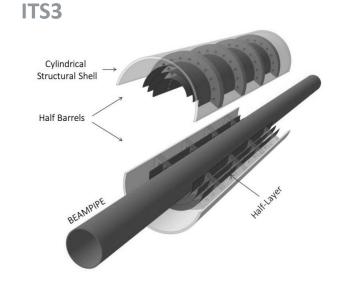


ALICE silicon tracker development path

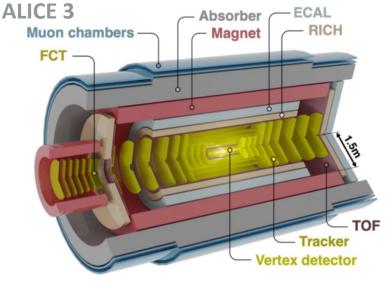








LOI: CERN-LHCC-2019-018



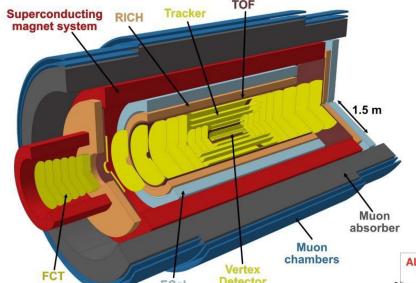
LOI: CERN-LHCC-2022-009
Scoping Document submitted to LHCC





ALICE 3



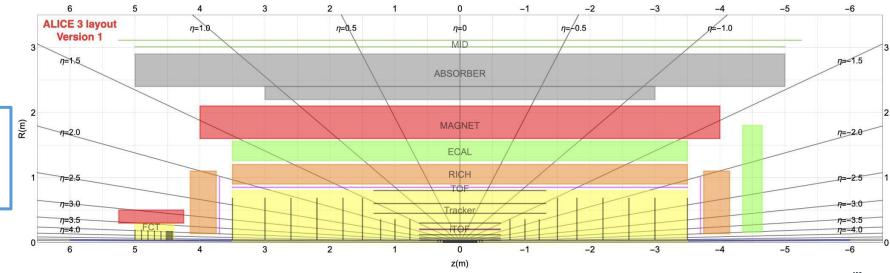


Next generation compact experiment for LHC Run 5 and beyond

- 60 m² low-mass all-silicon tracker fully made of MAPS
- Retractable vertex detector for unprecedented pointing resolution
- Large acceptance: $-4 < \eta < 4$
- Specific INFN R&D for Vertex Detector and Middle Layers



- Scoping Document submitted to LHCC
- Specific R&D has started



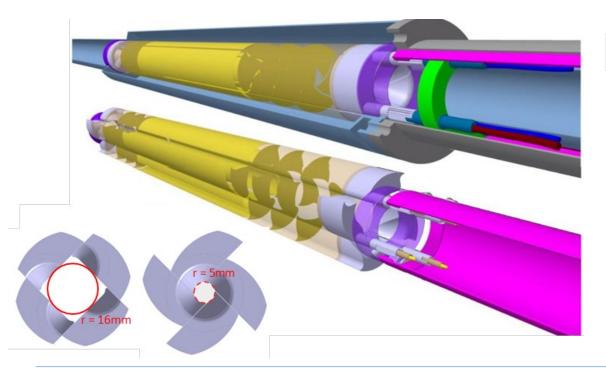


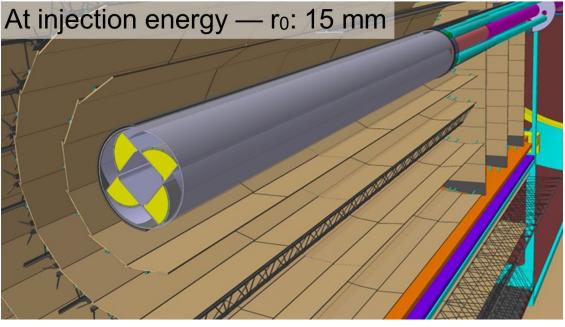
ALICE 3 Vertex Detector



3 barrel layers of ultra-thin, curved, wafer-scale MAPS

- Retractable structure inside the beam pipe secondary vacuum
- First detection layer at 5 mm from the interaction point
- Completed by 2 x 3 end-cap disks for high |η| coverage







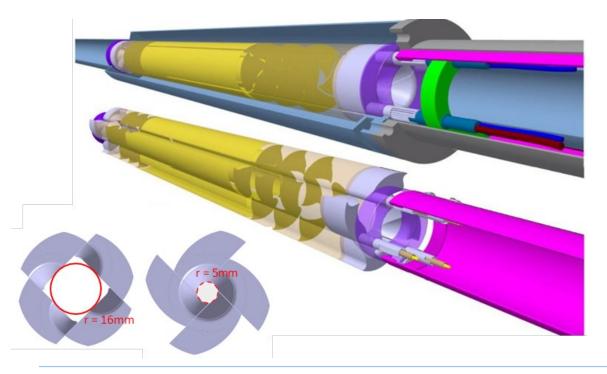


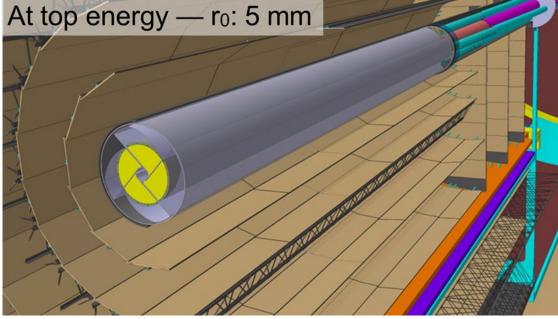
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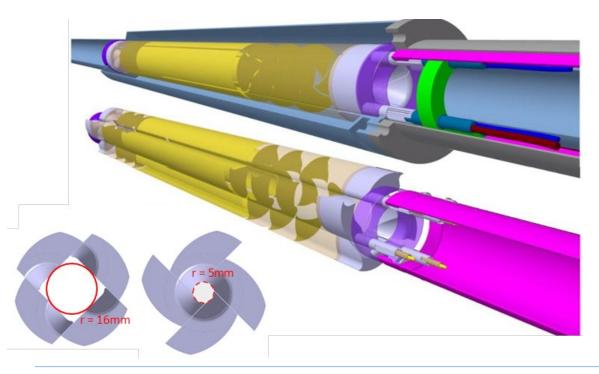


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3 barrel layers of ultra-thin, curved, wafer-scale MAPS

- Retractable structure inside the beam pipe secondary vacuum
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- Unprecedented spatial resolution: 2.5 μm
- Extremely low material budget: 0.1% X₀/layer
- Hit rate: up to 94 MHz cm⁻²
- Main R&D challenges:
 - Radiation hardness
 - 10¹⁶ 1MeV n_{eq} cm⁻² + 300 Mrad (LOI values)
 - In-vacuum mechanics and cooling
 - 10 µm pixel pitch
 - Data and power distribution



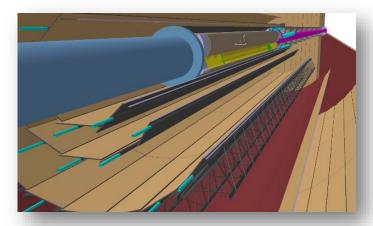


ALICE 3 Middle Layers and Outer Tracker

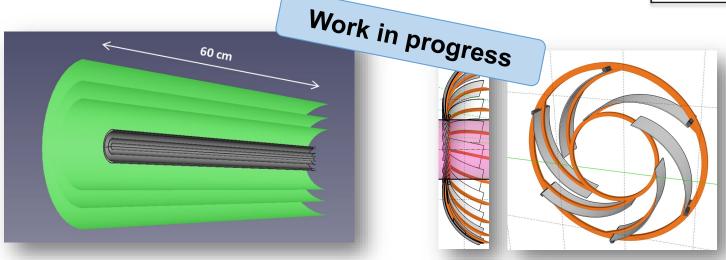


- Specific layouts being proposed for Middle Layers
 - 3-4 layers **outside the beam pipe** (r < 20 cm)
 - Material budget reduction from 1% to 0.1% beneficial for secondary particles and soft e





Standard staves/module layout (LOI)



ITS3-like bent large-area sensors

Blade/wheel barrels and disks

- Vertex Detector, Middle Layers and Outer Tracker need specific sensor optimizations:
 - Towards a common, versatile R&D path forking into two separate chips
 - Easier for other applications like FCC-ee to build on it







Conclusions and Outlook



- ALICE Upgrades for LS3 and LS4 targeting ambitious detector performance
- ITS3: ultra-thin, truly cylindrical, wafer-scale MAPS vertex detector for Run 4
- ALICE 3, future LHC heavy-ion collider experiment for Run 5 and beyond
- ITS3 and ALICE 3 upgrades can serve as stepping stones towards FCC-ee

Constant effort to encourage collaboration and exchange of information...





Regular occasions for discussion in 2024



ALICE tracker experts invited to several workshop to investigate MAPS silicon technology application to FCC-ee vertex and tracker:

RD FCC WP-Silicon Mini-workshop 22-23 Apr '24 - Torino

FCC Week 2024 10-14 Jun '24 - San Francisco (USA)

MAPS detectors technologies for the FCC-ee vertex 1 Jul '24 - CERN

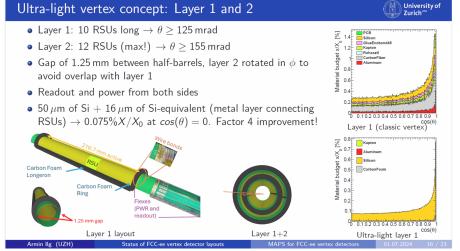
2nd FCC Italy & France Workshop 4-6 Nov 2024 - Venezia

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➤ Next steps:

- > Expressions of Interest in preparation
- ➤ Couple DRD3 and DRD7 activities with ALICE 3 MAPS development

Ultra-light vertex concept: Layer 1 and 2









Thank you for your attention!





Backup





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ALICE Upgrades' motivations and requirements



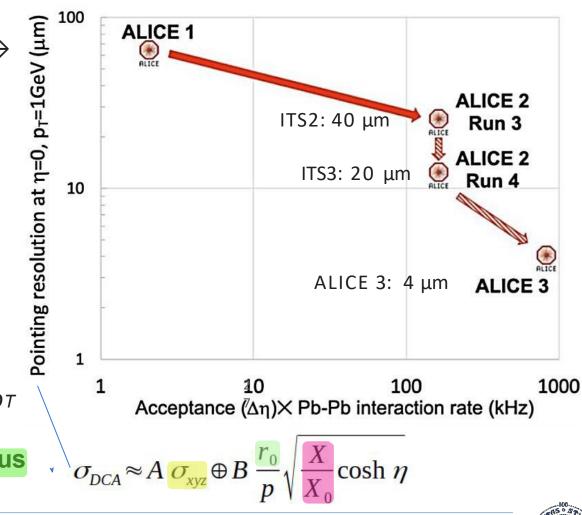
Physics Motivations:

Study of QGP in ultra-relativistic heavy-ions collisions search for rare, low momentum probes, reconstruction of displaced decay topologies:

- Heavy flavour hadrons at low p_T
- Thermal dileptons
- Precision measurements of light (hyper)nuclei and searches for charmed hypernuclei

Tracker upgrade requirements:

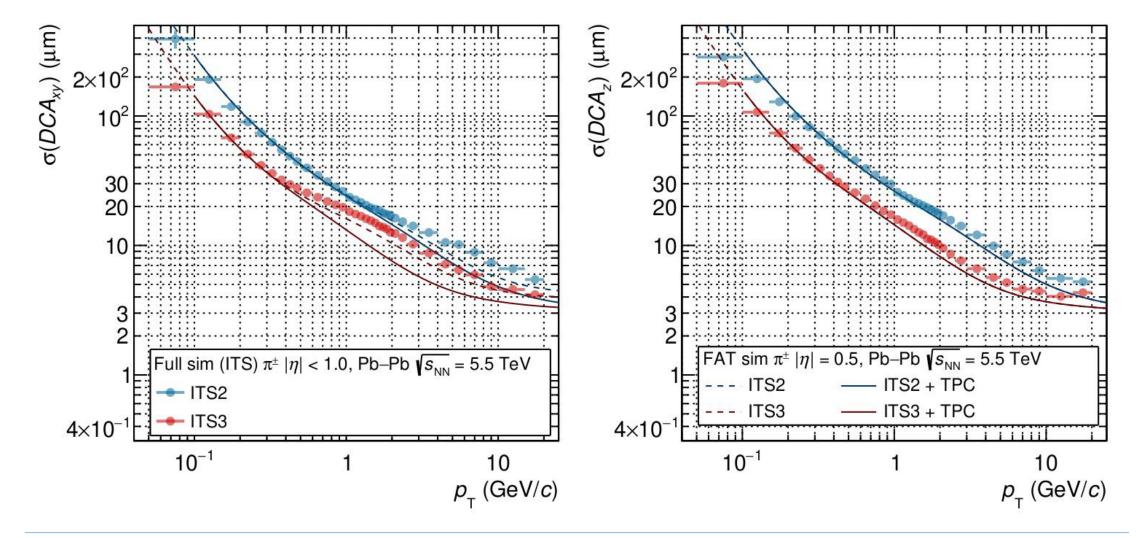
- Increase of effective acceptance (acceptance x readout rate)
- Improve tracking and vertexing performance low $p\tau$ for combinatorial background suppression
 - →Excellent spatial resolution, minimal inner radius and low material budget are needed





ITS3 pointing resolution





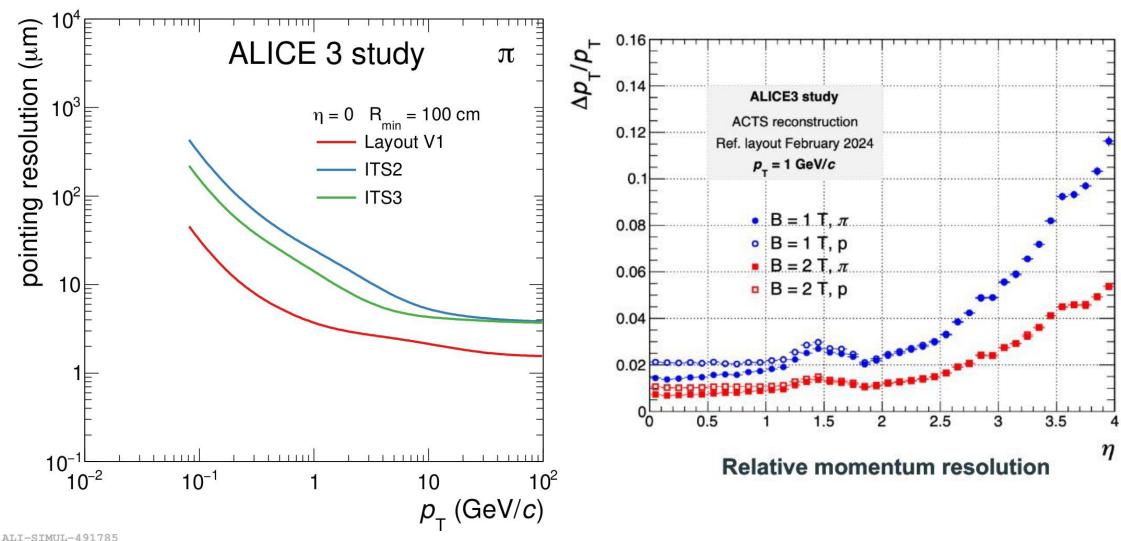




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ALICE 3 tracking performance









65 nm CMOS process validation and radiation hardness



TPSCo 65 nm CMOS process validated on MLR1 test structures:

FCC-ee

 $\sim 6 \times 10^{12} 1$ MeV neq /cm²/year

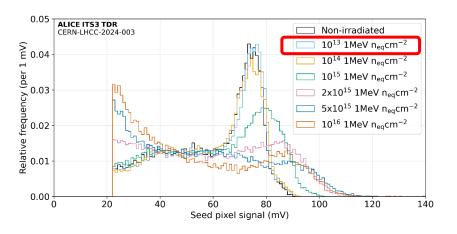


Efficient charge collection

Radiation hardness demonstrated beyond 10 kGy + 10¹³ 1MeV n_{eq} cm⁻²

ITS3 requirement

• Still efficient with 10¹⁵ 1MeV n_{eq} cm⁻² at room temperature





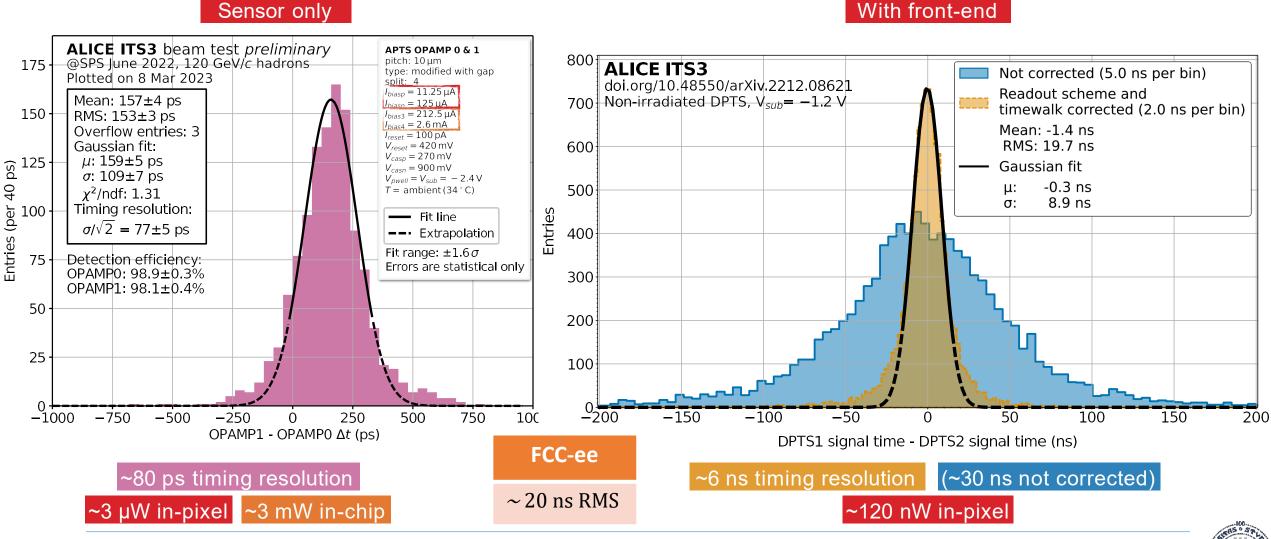
Seed **pixel signal response to** ⁵⁵**Fe** Vs irradiation levels, as measured on 15 μ m pitch **Analog Pixel Test Structures (APTS)**





ITS3 sensor performance: intrinsic time resolution



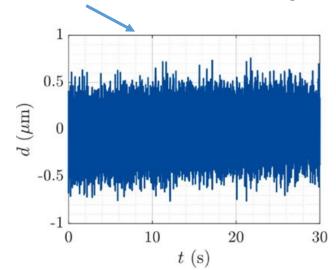


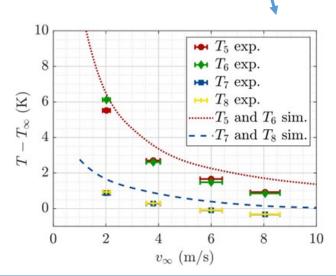


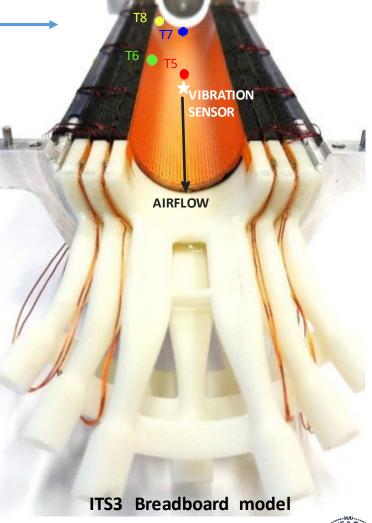
ITS3 air cooling studies



- Tests in wind tunnel on breadboard model
 - Dummy silicon sensor with copper serpentine heater
 - Thermal load: 25 mW cm⁻² in matrix, 1000 mW cm⁻² in end-caps
- Temperature difference from inlet and within the sensor < 5°C
 with 8 m/s airflow between the layers
- Mechanical assembly with carbon foam half rings keeps
 vibrations within ± 0.5 μm with 8 m/s airflow











ALICE 3 Middle Layers and Outer Tracker



60 m² of silicon

- 8 barrel layers (3.5 cm < radius < 80 cm)
- 2 x 9 end-cap disks
- Material budget: 1% X₀/layer
- Position resolution: 10 μm (~ 50 μm pixel pitch)
- Low power consumption < 20 mW/cm²
- 100 ns time resolution to mitigate pile-up

Main R&D challenges:

- Module design for industrialized production
- Low power consumption while preserving timing performance

